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Triacs

BT138 series

GENERAL DESCRIPTION

Passivated triacs in a plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

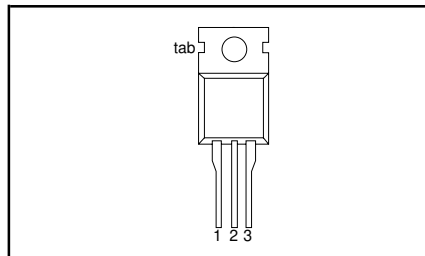
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages	600 600F 600G 600	800 800F 800G 800	V
$I_{\text{T(RMS)}}$	RMS on-state current	12	12	A
I_{TSM}	Non-repetitive peak on-state current	95	95	A

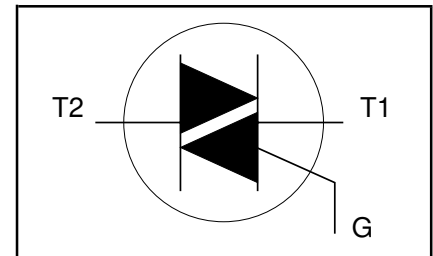
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-600 600 ¹	-800 800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 99\text{ }^{\circ}\text{C}$	-	12		A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_{\text{j}} = 25\text{ }^{\circ}\text{C}$ prior to surge $t = 20\text{ ms}$	-	95		A
		$t = 16.7\text{ ms}$	-	105		A
I^2t	I^2t for fusing	$t = 10\text{ ms}$	-	45		A ² s
di_{T}/dt	Repetitive rate of rise of on-state current after triggering	$I_{\text{TM}} = 20\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	50		A/ μs
		T2+ G+	-	50		A/ μs
		T2+ G-	-	50		A/ μs
		T2- G-	-	50		A/ μs
		T2- G+	-	10		A/ μs
I_{GM}	Peak gate current		-	2		A
V_{GM}	Peak gate voltage		-	5		V
P_{GM}	Peak gate power		-	5		W
$P_{\text{G(AV)}}$	Average gate power	over any 20 ms period	-	0.5		W
T_{stg}	Storage temperature		-40	150		$^{\circ}\text{C}$
T_{j}	Operating junction temperature		-	125		$^{\circ}\text{C}$

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle in free air	-	-	2.0	K/W
			-	60	-	K/W

STATIC CHARACTERISTICS

 $T_j = 25\ ^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.			UNIT
I_{GT}	Gate trigger current	BT138- $V_D = 12\ \text{V}; I_T = 0.1\ \text{A}$ T2+ G+ T2+ G- T2- G- T2- G+	- - - -	5 8 10 22	35 35 35 70	25 25 25 70	50 50 50 100	mA mA mA mA
I_L	Latching current	$V_D = 12\ \text{V}; I_{GT} = 0.1\ \text{A}$ T2+ G+ T2+ G- T2- G- T2- G+	- - - -	7 20 8 10	40 60 40 60	40 60 40 60	60 90 60 90	mA mA mA mA
I_H	Holding current	$V_D = 12\ \text{V}; I_{GT} = 0.1\ \text{A}$	-	6	30	30	60	mA
V_T	On-state voltage	$I_T = 15\ \text{A}$	-	1.4	1.65			V
V_{GT}	Gate trigger voltage	$V_D = 12\ \text{V}; I_T = 0.1\ \text{A}$ $V_D = 400\ \text{V}; I_T = 0.1\ \text{A};$ $T_j = 125\ ^\circ\text{C}$	- 0.25	0.7 0.4	1.5 -			V V
I_D	Off-state leakage current	$V_D = V_{DRM(max)};$ $T_j = 125\ ^\circ\text{C}$	-	0.1	0.5			mA

DYNAMIC CHARACTERISTICS

 $T_j = 25\ ^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.			TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	BT138- $V_{DM} = 67\% V_{DRM(max)};$ $T_j = 125\ ^\circ\text{C};$ exponential waveform; gate open circuit	100	50	200	250	-	V/ μs
dV_{com}/dt	Critical rate of change of commutating voltage	$V_{DM} = 400\ \text{V}; T_j = 95\ ^\circ\text{C};$ $I_{T(RMS)} = 12\ \text{A};$ $dI_{com}/dt = 5.4\ \text{A/ms};$ gate open circuit	-	-	10	20	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 16\ \text{A}; V_D = V_{DRM(max)};$ $I_G = 0.1\ \text{A}; dI_G/dt = 5\ \text{A}/\mu\text{s}$	-	-	-	2	-	μs

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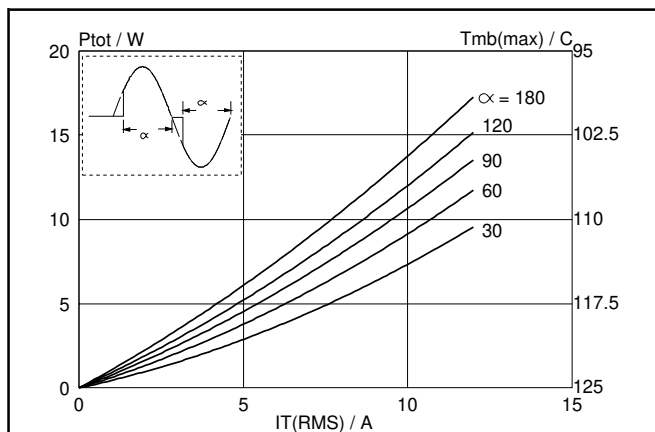


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

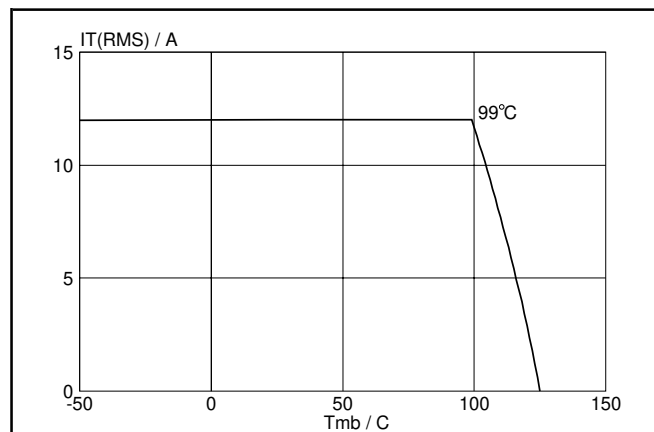


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

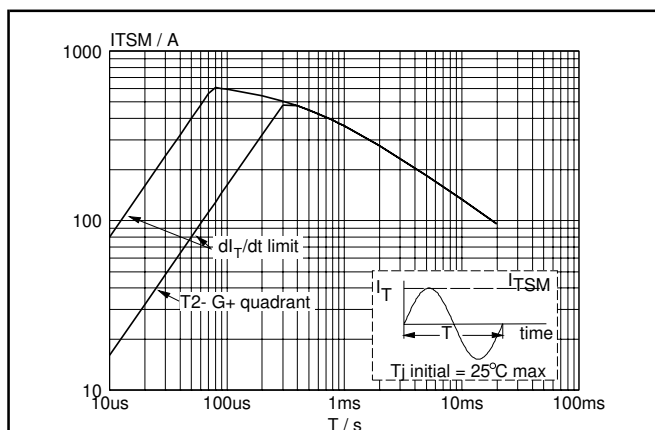


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20$ ms.

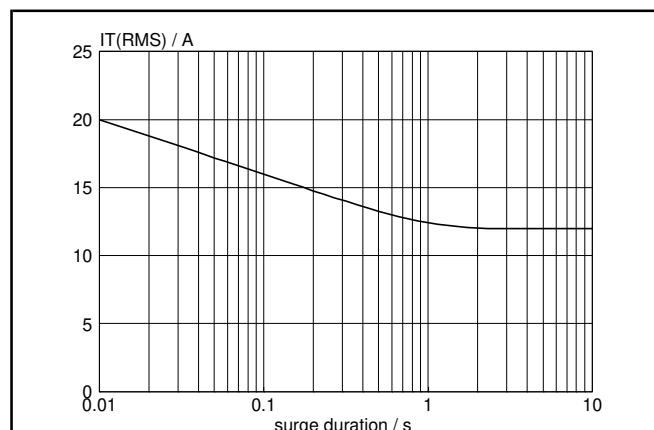


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50$ Hz; $T_{mb} \leq 99^\circ\text{C}$.

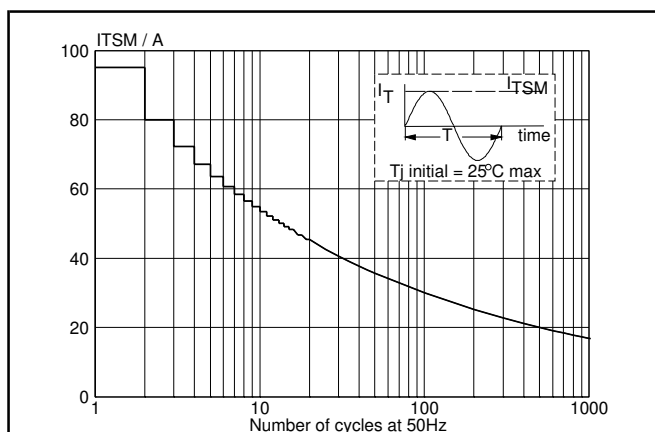


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50$ Hz.

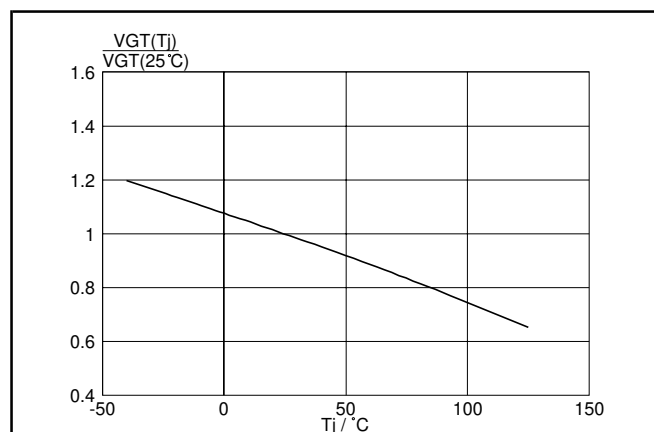


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

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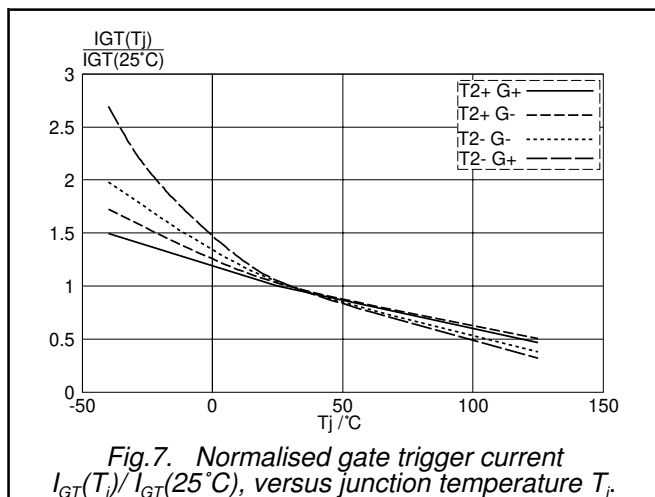


Fig. 7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

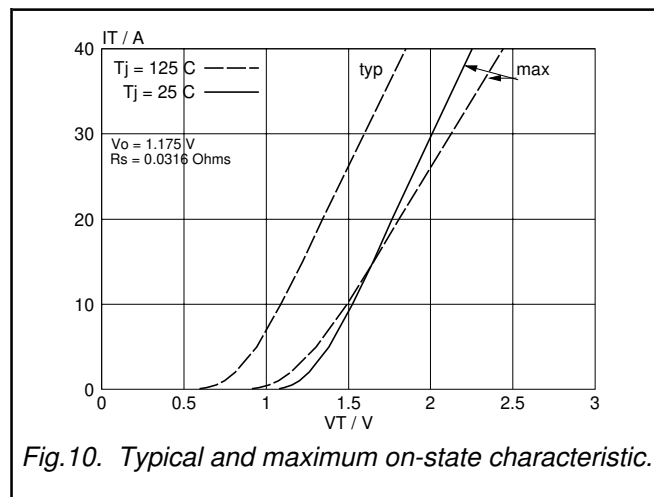


Fig. 10. Typical and maximum on-state characteristic.

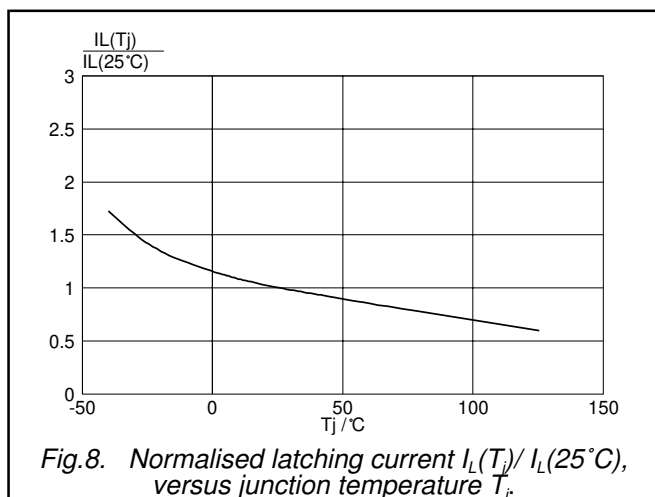


Fig. 8. Normalised latching current $I_L(T_j)/I_L(25^\circ\text{C})$, versus junction temperature T_j .

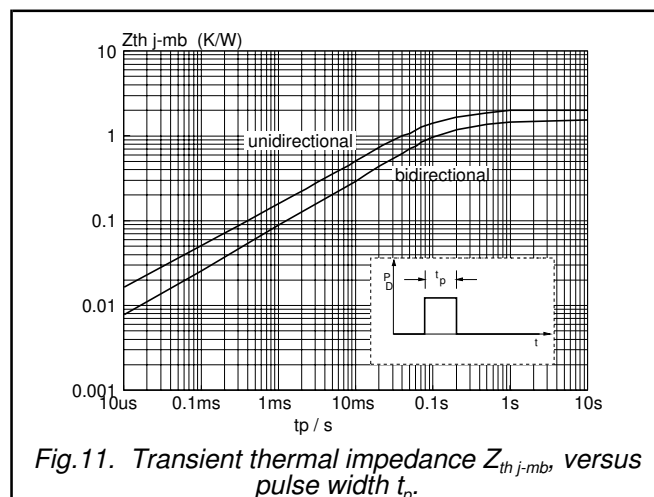


Fig. 11. Transient thermal impedance $Z_{th\ j-mb}$, versus pulse width t_p .

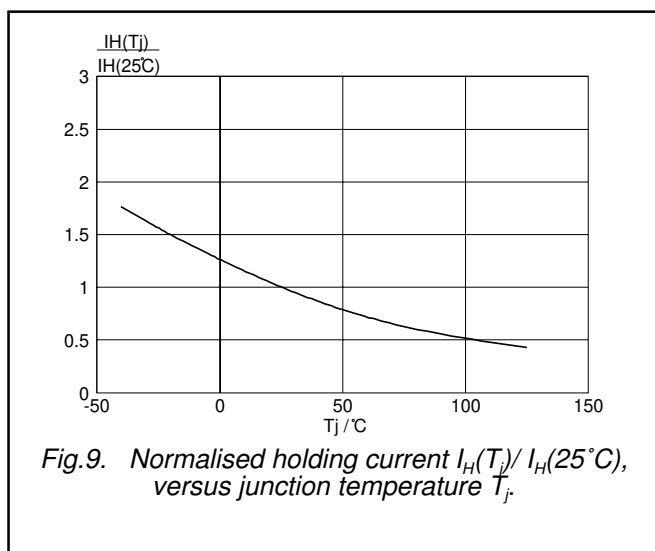


Fig. 9. Normalised holding current $I_H(T_j)/I_H(25^\circ\text{C})$, versus junction temperature T_j .

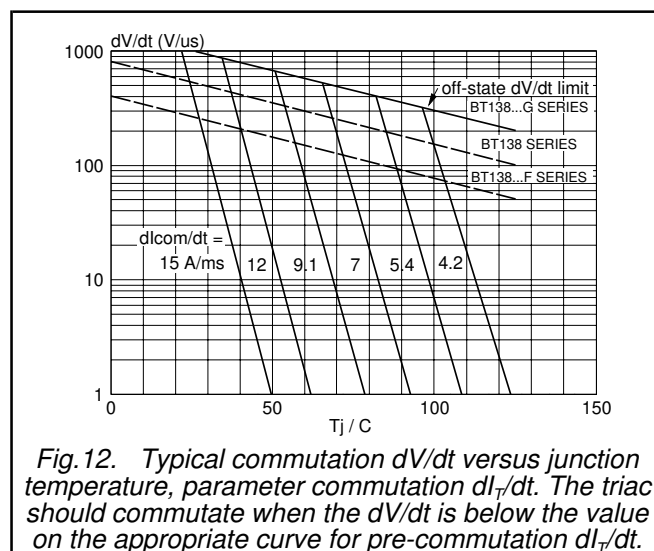


Fig. 12. Typical commutation dV/dt versus junction temperature, parameter commutation dI_T/dt . The triac should commute when the dV/dt is below the value on the appropriate curve for pre-commutation dI_T/dt .

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

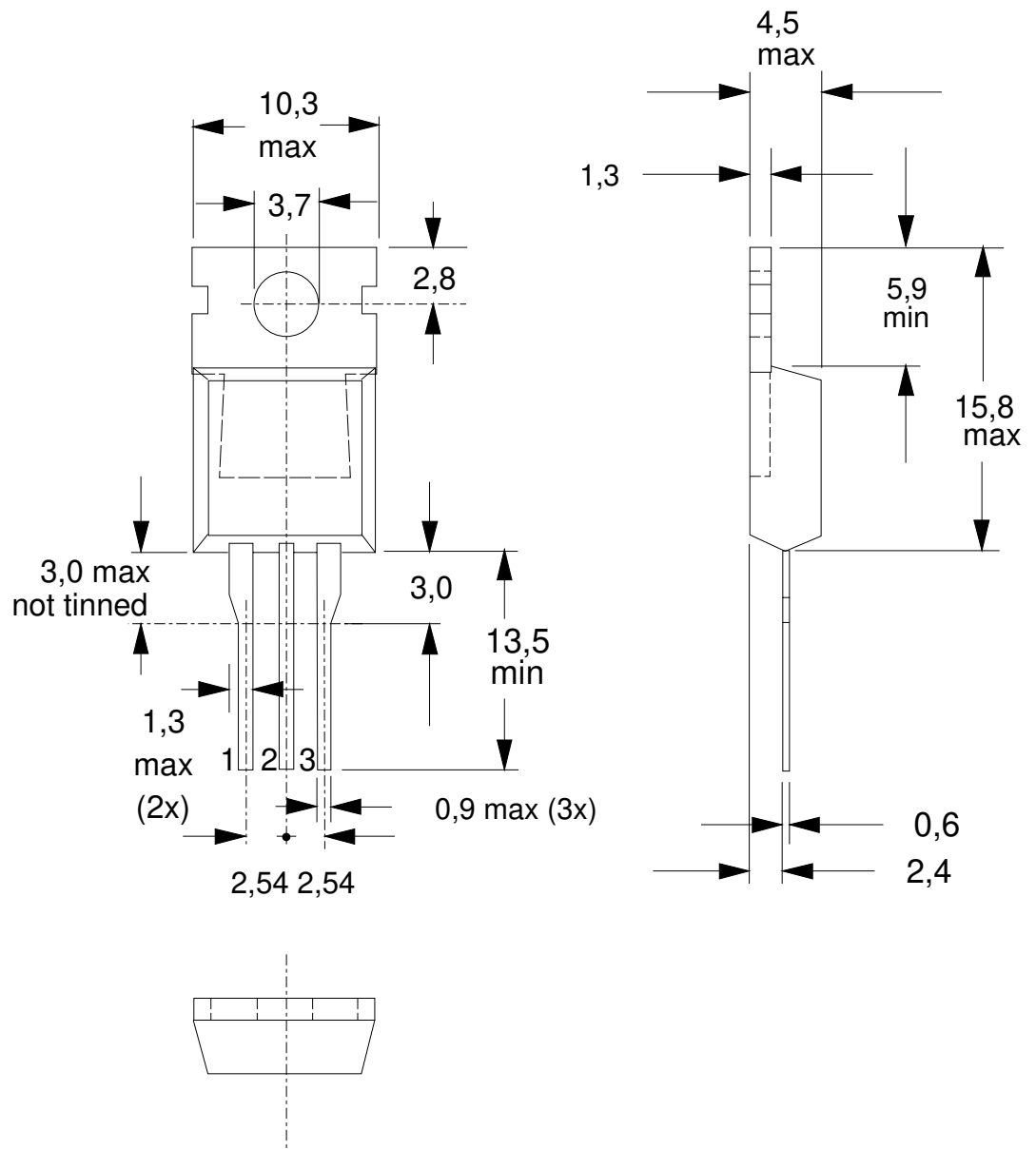


Fig.13. SOT78 (TO220AB). pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

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DATA SHEET STATUS²	PRODUCT STATUS³	DEFINITIONS
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Application information		
Where application information is given, it is advisory and does not form part of the specification.		
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